

AMENDMENT TO THE CLAIMS

1-11. (Cancelled)

12. (Currently amended) A method manufacturing a semiconductor device, comprising the sequential steps of:

forming first and second transistors on a main surface of a semiconductor substrate with a space between each other;

forming first metal silicide at a surface of a source/drain of said second transistor with a source/drain of said first transistor being covered by an insulating film;

forming an interlayer insulating film covering said first and second transistors;

forming in said interlayer insulating film a first contact hole reaching one of said source/drain of said first transistor;

forming a plug electrode in said first contact hole;

forming in said interlayer insulating film a second contact hole reaching one of said source/drain of said second transistor;

forming second metal silicide on said plug electrode;

forming a bit line on said second metal silicide and an interconnection in said second contact hole.

13. (Cancelled)